

1. Number	2. Hits	3. Search Text	4. USPAT;	5. TIME STAMP
1	1739	((high near (dielectric insulat\$3) near constant).ti.)	USPAT; US-PPGPUB; EPO; JPO; DEPWENT; IBM TDB USPAT; US-PPGPUB; EPO; JPO; DEPWENT; IBM TDB	2003/01/21 10:36
2	134	((high near (dielectric insulat\$3) near constant).ti.) and (gap cavity groove opening recess trench)	USPAT; US-PPGPUB; EPO; JPO; DEPWENT; IBM TDB	2003/01/21 10:46
3	156	((high near (dielectric insulat\$3) near constant).ti.) and (gap cavity groove opening recess trench) and (substrate wafer pad base)	USPAT; US-PPGPUB; EPO; JPO; DEPWENT; IBM TDB	2003/01/21 10:46
4	122	((((high near (dielectric insulat\$3) near constant).ti.) and (gap cavity groove opening recess trench)) and (substrate wafer pad base)) and @ad<20000526	USPAT; US-PPGPUB; EPO; JPO; DEPWENT; IBM TDB	2003/01/21 09:54
5	94	(((((high near (dielectric insulat\$3) near constant).ti.) and (gap cavity groove opening recess trench)) and (substrate wafer pad base)) and @ad<20000526) and capacitor	USPAT; US-PPGPUB; EPO; JPO; DEPWENT; IBM TDB	2003/01/21 10:10
6	25	(((((high near (dielectric insulat\$3) near constant).ti.) and (gap cavity groove opening recess trench)) and (substrate wafer pad base)) and @ad<20000526) and capacitor) and conductor	USPAT; US-PPGPUB; EPO; JPO; DEPWENT; IBM TDB	2003/01/21 10:10
7	43095	high near (dielectric insulat\$3 K)	USPAT; US-PPGPUB; EPO; JPO; DEPWENT; IBM TDB	2003/01/21 10:34
8	16877	(high near (dielectric insulat\$3 K)) and (gap cavity groove opening recess trench)	USPAT; US-PPGPUB; EPO; JPO; DEPWENT; IBM TDB	2003/01/21 10:41
9	1656	((high near (dielectric insulat\$3 K)) and (gap cavity groove opening recess trench)) and (interlayer (inter near1 layer))	USPAT; US-PPGPUB; EPO; JPO; DEPWENT; IBM TDB	2003/01/21 10:45
10	1624	((high near (dielectric insulat\$3 K)) and (gap cavity groove opening recess trench)) and (interlayer (inter near1 layer)) and (metal wir\$3 conduct\$3)	USPAT; US-PPGPUB; EPO; JPO; DEPWENT; IBM TDB	2003/01/21 10:47
11	993	((high near (dielectric insulat\$3 K)) and (gap cavity groove opening recess trench)) and (interlayer (inter near1 layer)) and (metal wir\$3 conduct\$3), and capacitor	USPAT; US-PPGPUB; EPO; JPO; DEPWENT; IBM TDB	2003/01/21 10:47
12	994	((high near (dielectric insulat\$3 K)) and (gap cavity groove opening recess trench)) and (interlayer (inter near1 layer)) and (metal wir\$3 conduct\$3)) and capacitor) and (substrate wafer pad base)	USPAT; US-PPGPUB; EPO; JPO; DEPWENT; IBM TDB	2003/01/21 10:46